

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK1328, 2SK1329

Silicon N-Channel MOS FET

RENESAS

ADE-208-1270 (Z)
1st. Edition
Mar. 2001

Application

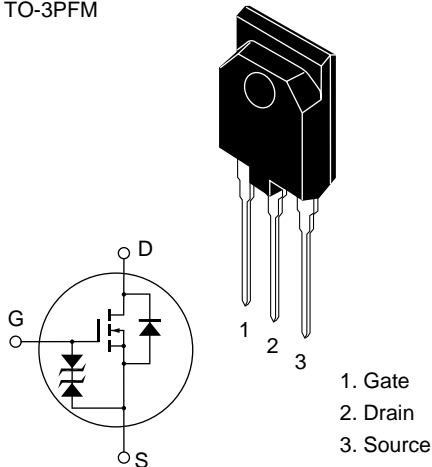
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

TO-3PFM



2SK1328, 2SK1329

Absolute Maximum Ratings (Ta = 25°C)

| Item | | Symbol | Ratings | Unit |
|---|---------|---------------------|-------------|------|
| Drain to source voltage | 2SK1328 | V_{DSS} | 450 | V |
| | 2SK1329 | | 500 | |
| Gate to source voltage | | V_{GSS} | ±30 | V |
| Drain current | | I_D | 12 | A |
| Drain peak current | | $I_{D(pulse)}^{*1}$ | 48 | A |
| Body to drain diode reverse drain current | | I_{DR} | 12 | A |
| Channel dissipation | | Pch^{*2} | 60 | W |
| Channel temperature | | Tch | 150 | °C |
| Storage temperature | | Tstg | -55 to +150 | °C |

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

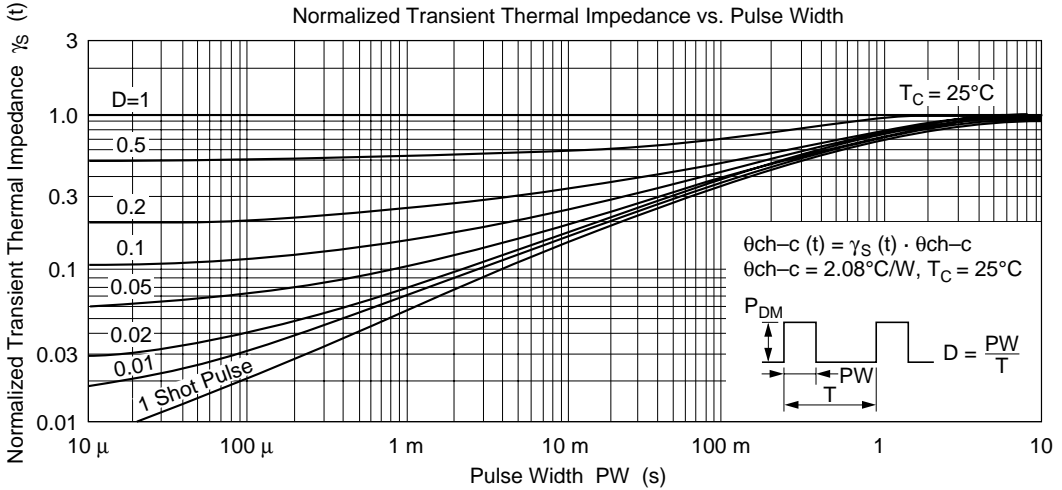
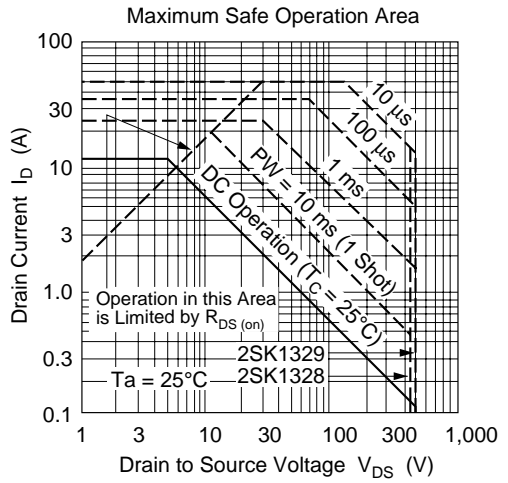
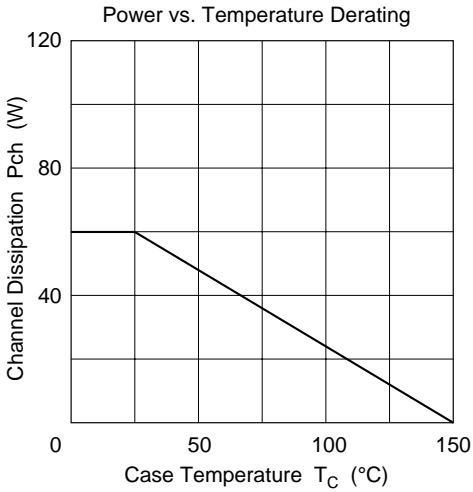
2. Value at $T_C = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|----------------------------------|------------|--------------|--------------|---------------|--|
| Drain to source breakdown voltage | 2SK1328 $V_{(BR)DSS}$ 2SK1329 | 450 500 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ± 30 | — | — | V | $I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ± 10 | μA | $V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$ |
| Zero gate voltage drain current | 2SK1328 I_{DSS} 2SK1329 | — | — | 250 | μA | $V_{DS} = 360 \text{ V}$, $V_{GS} = 0$ $V_{DS} = 400 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 2.0 | — | 3.0 | V | $I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$ |
| Static Drain to source on state resistance | 2SK1328 $R_{DS(on)}$ 2SK1329 | — | 0.40 0.45 | 0.55 0.60 | Ω | $I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$ |
| Forward transfer admittance | $ y_{fs} $ | 6.0 | 10 | — | S | $I_D = 6 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$ |
| Input capacitance | C_{iss} | — | 1450 | — | pF | $V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, |
| Output capacitance | C_{oss} | — | 410 | — | pF | $f = 1 \text{ MHz}$ |
| Reverse transfer capacitance | C_{rss} | — | 55 | — | pF | |
| Turn-on delay time | $t_{d(on)}$ | — | 20 | — | ns | $I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$, |
| Rise time | t_r | — | 70 | — | ns | $R_L = 5 \text{ }\Omega$ |
| Turn-off delay time | $t_{d(off)}$ | — | 120 | — | ns | |
| Fall time | t_f | — | 60 | — | ns | |
| Body to drain diode forward voltage | V_{DF} | — | 1.0 | — | V | $I_F = 12 \text{ A}$, $V_{GS} = 0$ |
| Body to drain diode reverse recovery time | t_{rr} | — | 450 | — | ns | $I_F = 12 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

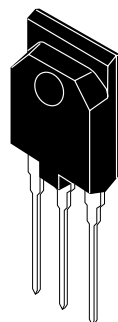
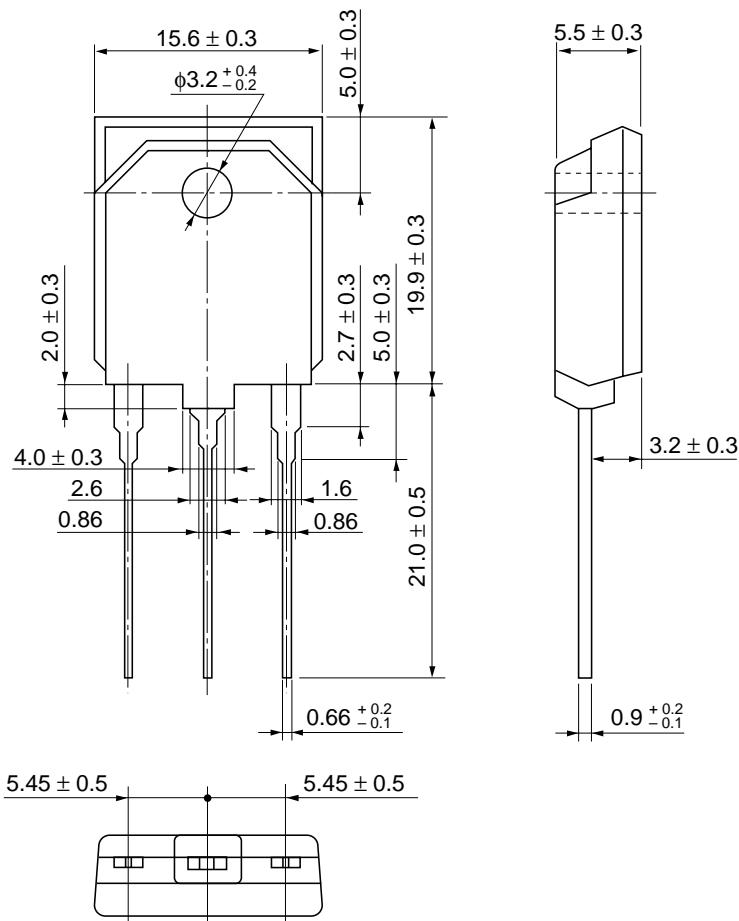
Note: 1. Pulse test

See characteristic curves of 2SK1165, 2SK1166.



Package Dimensions

As of January, 2001
Unit: mm



| | |
|------------------------|---------|
| Hitachi Code | TO-3PFM |
| JEDEC | — |
| EIAJ | — |
| Mass (reference value) | 5.2 g |

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

| | | | |
|-----|--------------|---|---|
| URL | NorthAmerica | : | http://semiconductor.hitachi.com/ |
| | Europe | : | http://www.hitachi-eu.com/hel/ecg |
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : <http://www.hitachi.com.hk>

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